

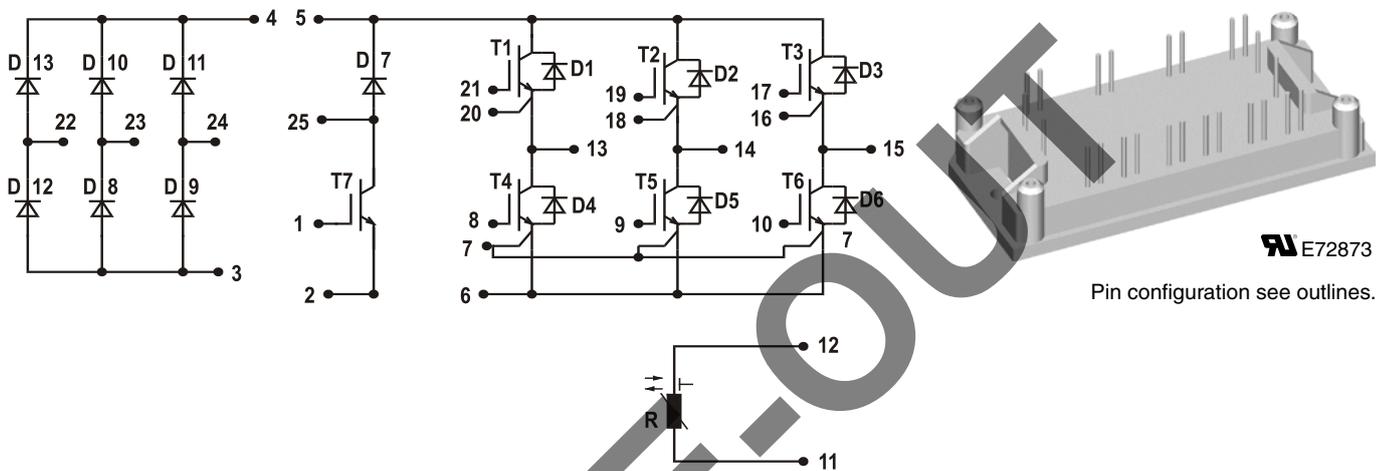
Converter - Brake - Inverter Module (CBI 1) NPT IGBT

Three Phase Rectifier	Brake Chopper	Three Phase Inverter
$V_{RRM} = 1600 \text{ V}$	$V_{CES} = 600 \text{ V}$	$V_{CES} = 600 \text{ V}$
$I_{DAVM25} = 95 \text{ A}$	$I_{C25} = 12 \text{ A}$	$I_{C25} = 31 \text{ A}$
$I_{FSM} = 250 \text{ A}$	$V_{CE(sat)} = 2.0 \text{ V}$	$V_{CE(sat)} = 2.1 \text{ V}$

Preliminary data

Part name (Marking on product)

MUBW25-06A6K



Features:

- High level of integration - only one power semiconductor module required for the whole drive
- Inverter with NPT IGBTs
- low saturation voltage
- positive temperature coefficient
- fast switching
- short tail current
- Epitaxial free wheeling diodes with hiperfast and soft reverse recovery
- Industry standard package with insulated copper base plate and soldering pins for PCB mounting
- Temperature sense included

Application:

- AC motor drives with
- Input from single or three phase grid
- Three phase synchronous or asynchronous motor
- Electric braking operation

Package:

- UL registered
- Industry standard E1-pack

Output Inverter T1 - T6

Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
V_{CES}	collector emitter voltage	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$			600	V
V_{GES}	max. DC gate voltage	continuous			± 20	V
V_{GEM}	max. transient collector gate voltage	transient			± 30	V
I_{C25}	collector current	$T_C = 25^{\circ}\text{C}$			31	A
I_{C80}		$T_C = 80^{\circ}\text{C}$			21	A
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$			100	W
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 20\text{ A}; V_{GE} = 15\text{ V}$			2.1 2.3	V V
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 0.5\text{ mA}; V_{GE} = V_{CE}$	4.5		6.5	V
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$			1.3	mA mA
I_{GES}	gate emitter leakage current	$V_{CE} = 0\text{ V}; V_{GE} = \pm 20\text{ V}$			100	nA
C_{ies}	input capacitance	$V_{CE} = 25\text{ V}; V_{GE} = 0\text{ V}; f = 1\text{ MHz}$			1100	pF
$Q_{G(on)}$	total gate charge	$V_{CE} = 300\text{ V}; V_{GE} = 15\text{ V}; I_C = 20\text{ A}$			65	nC
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 300\text{ V}; I_C = 20\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 47\ \Omega$				
t_r	current rise time					
$t_{d(off)}$	turn-off delay time					
t_f	current fall time					
E_{on}	turn-on energy per pulse					
E_{off}	turn-off energy per pulse					
I_{CM}	reverse bias safe operating area	RBSOA; $V_{GE} = \pm 15\text{ V}; R_G = 47\ \Omega$ $L = 100\ \mu\text{H};$ clamped induct. load $V_{CEmax} = V_{CES} - L_S \cdot di/dt$	$T_{VJ} = 125^{\circ}\text{C}$		40	A
t_{SC} (SCSOA)	short circuit safe operating area	$V_{CE} = 600\text{ V}; V_{GE} = \pm 15\text{ V}; R_G = 47\ \Omega;$ non-repetitive	$T_{VJ} = 125^{\circ}\text{C}$		10	μs
R_{thJC}	thermal resistance junction to case	(per IGBT)			1.25	K/W
R_{thCH}	thermal resistance case to heatsink	(per IGBT)			0.45	K/W

Output Inverter D1 - D6

Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
V_{RRM}	max. repetitive reverse voltage	$T_{VJ} = 150^{\circ}\text{C}$			600	V
I_{F25}	forward current	$T_C = 25^{\circ}\text{C}$			36	A
I_{F80}		$T_C = 80^{\circ}\text{C}$			24	A
V_F	forward voltage	$I_F = 20\text{ A}; V_{GE} = 0\text{ V}$			2.2	V
I_{RM}	max. reverse recovery current	$V_R = 300\text{ V}$ $di_f/dt = -400\text{ A}/\mu\text{s}$ $I_F = 20\text{ A}; V_{GE} = 0\text{ V}$				
t_{rr}	reverse recovery time					
$E_{rec(off)}$	reverse recovery energy					
R_{thJC}	thermal resistance junction to case	(per diode)			1.6	K/W
R_{thCH}	thermal resistance case to heatsink	(per diode)			0.55	K/W

 $T_C = 25^{\circ}\text{C}$ unless otherwise stated

Brake Chopper T7

Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
V_{CES}	collector emitter voltage		$T_{VJ} = 25^{\circ}\text{C}$ to 150°C			V
V_{GES}	max. DC gate voltage	continuous			± 20	V
V_{GEM}	max. transient collector gate voltage	transient			± 30	V
I_{C25}	collector current		$T_C = 25^{\circ}\text{C}$			A
I_{C80}			$T_C = 80^{\circ}\text{C}$			A
P_{tot}	total power dissipation		$T_C = 25^{\circ}\text{C}$			W
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 10\text{ A}; V_{GE} = 15\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$			V V
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 0.35\text{ mA}; V_{GE} = V_{CE}$	3		5	V
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$			mA mA
I_{GES}	gate emitter leakage current	$V_{CE} = 0\text{ V}; V_{GE} = \pm 20\text{ V}$			100	nA
C_{ies}	input capacitance	$V_{CE} = 25\text{ V}; V_{GE} = 0\text{ V}; f = 1\text{ MHz}$		600		pF
$Q_{G(on)}$	total gate charge	$V_{CE} = 300\text{ V}; V_{GE} = 15\text{ V}; I_C = 10\text{ A}$		39		nC
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 300\text{ V}; I_C = 10\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 82\ \Omega$	$T_{VJ} = 125^{\circ}\text{C}$			ns
t_r	current rise time		35		ns	
$t_{d(off)}$	turn-off delay time		40		ns	
t_f	current fall time		230		ns	
E_{on}	turn-on energy per pulse		30		mJ	
E_{off}	turn-off energy per pulse		0.4		mJ	
I_{CM}	reverse bias safe operating area	RBSOA; $V_{GE} = \pm 15\text{ V}; R_G = 82\ \Omega$ $L = 100\ \mu\text{H};$ clamped induct. load $V_{CEmax} = V_{CES} - L_S \cdot di/dt$	$T_{VJ} = 125^{\circ}\text{C}$			A
t_{SC} (SCSOA)	short circuit safe operating area	$V_{CE} = 600\text{ V}; V_{GE} = \pm 15\text{ V};$ $R_G = 82\ \Omega;$ non-repetitive	$T_{VJ} = 125^{\circ}\text{C}$			μs
R_{thJC}	thermal resistance junction to case	(per IGBT)			1.7	K/W
R_{thCH}	thermal resistance case to heatsink	(per IGBT)		0.55		K/W

Brake Chopper D7

Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
V_{RRM}	max. repetitive reverse voltage		$T_{VJ} = 150^{\circ}\text{C}$			V
I_{F25}	forward current		$T_C = 25^{\circ}\text{C}$			A
I_{F80}			$T_C = 80^{\circ}\text{C}$			A
V_F	forward voltage	$I_F = 10\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$			V V
I_R	reverse current	$V_R = V_{RRM}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$			mA mA
I_{RM}	max. reverse recovery current	$V_R = 300\text{ V}; I_F = 10\text{ A}$ $di_f/dt = -400\text{ A}/\mu\text{s}$	$T_{VJ} = 100^{\circ}\text{C}$			A
t_{rr}	reverse recovery time		12		ns	
R_{thJC}	thermal resistance junction to case	(per diode)			2.5	K/W
R_{thCH}	thermal resistance case to heatsink	(per diode)		0.85		K/W

 $T_C = 25^{\circ}\text{C}$ unless otherwise stated

Input Rectifier Bridge D8 - D13					
Symbol	Definitions	Conditions	Maximum Ratings		
V_{RRM}	max. repetitive reverse voltage			1600	V
I_{FAV}	average forward current	sine 180°	$T_C = 80^\circ\text{C}$	23	A
I_{DAVM}	max. average DC output current	rectangular; $d = 1/3$; bridge	$T_C = 80^\circ\text{C}$	65	A
I_{FSM}	max. surge forward current	$t = 10\text{ ms}$; sine 50 Hz	$T_C = 25^\circ\text{C}$	250	A
P_{tot}	total power dissipation		$T_C = 25^\circ\text{C}$	65	W

Symbol	Conditions	Characteristic Values				
		min.	typ.	max.		
V_F	forward voltage	$I_F = 30\text{ A}$	$T_{VJ} = 25^\circ\text{C}$	1.1	1.45	V
			$T_{VJ} = 125^\circ\text{C}$	1.2		V
I_R	reverse current	$V_R = V_{RRM}$	$T_{VJ} = 25^\circ\text{C}$	0.4	0.02	mA
			$T_{VJ} = 125^\circ\text{C}$			mA
R_{thJC}	thermal resistance junction to case	(per diode)	$T_{VJ} = 25^\circ\text{C}$		1.9	K/W
R_{thCH}	thermal resistance case to heatsink	(per diode)		0.65		K/W

Temperature Sensor NTC							
Symbol	Definitions	Conditions	Ratings			Unit	
			min.	typ.	max.		
R_{25}	resistance		$T_C = 25^\circ\text{C}$	4.45	4.7	5.0	k Ω
$B_{25/85}$					3510		K

Module						
Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
T_{VJ}	operating temperature		-40		125	$^\circ\text{C}$
T_{VJM}	max. virtual junction temperature				150	$^\circ\text{C}$
T_{stg}	storage temperature		-40		125	$^\circ\text{C}$
V_{ISOL}	isolation voltage	$I_{ISOL} \leq 1\text{ mA}$; 50/60 Hz			2500	V~
M_d	mounting torque	(M4)	2.0		2.2	Nm
d_S	creep distance on surface		12.7			mm
d_A	strike distance through air		12.7			mm
Weight				40		g

Equivalent Circuits for Simulation						
Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
V_0	rectifier diode	D8 - D13	$T_{VJ} = 125^\circ\text{C}$	0.90		V
R_0				12		m Ω
V_0	IGBT	T1 - T6	$T_{VJ} = 125^\circ\text{C}$	1.0		V
R_0				50		m Ω
V_0	free wheeling diode	D1 - D6	$T_{VJ} = 125^\circ\text{C}$	1.25		V
R_0				13		m Ω
V_0	IGBT	T7	$T_{VJ} = 125^\circ\text{C}$	1.0		V
R_0				110		m Ω
V_0	free wheeling diode	D7	$T_{VJ} = 125^\circ\text{C}$	1.25		V
R_0				26		m Ω

$T_C = 25^\circ\text{C}$ unless otherwise stated

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